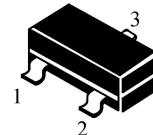


**SOT-23 Bipolar Transistor 双极型三极管****■Features 特点****NPN General Purpose 通用****SOT-23**

1. BASE
- 
2. Emitter
- 
3. Collector

**■Absolute Maximum Ratings 最大额定值**

Characteristic 特性参数	Symbol 符号	BC846 A/B/C	BC847 A/B/C	BC848 A/B/C	Unit 单位
Collector-Base Voltage 集电极基极电压	V <sub>CBO</sub>	80	50	30	V
Collector-Emitter Voltage 集电极发射极电压	V <sub>CEO</sub>	65	45	30	V
Emitter-Base Voltage 发射极基极电压	V <sub>EBO</sub>	6	6	5	V
Collector Current 集电极电流	I <sub>C</sub>		100		mA
Power dissipation 耗散功率	P <sub>C</sub> (T <sub>a</sub> =25°C)		200		mW
Thermal Resistance Junction-Ambient 热阻	R <sub>θJA</sub>		625		°C/W
Junction and Storage Temperature 结温和储藏温度	T <sub>J</sub> , T <sub>stg</sub>		-55 to +150°C		

**■Device Marking 产品打标**

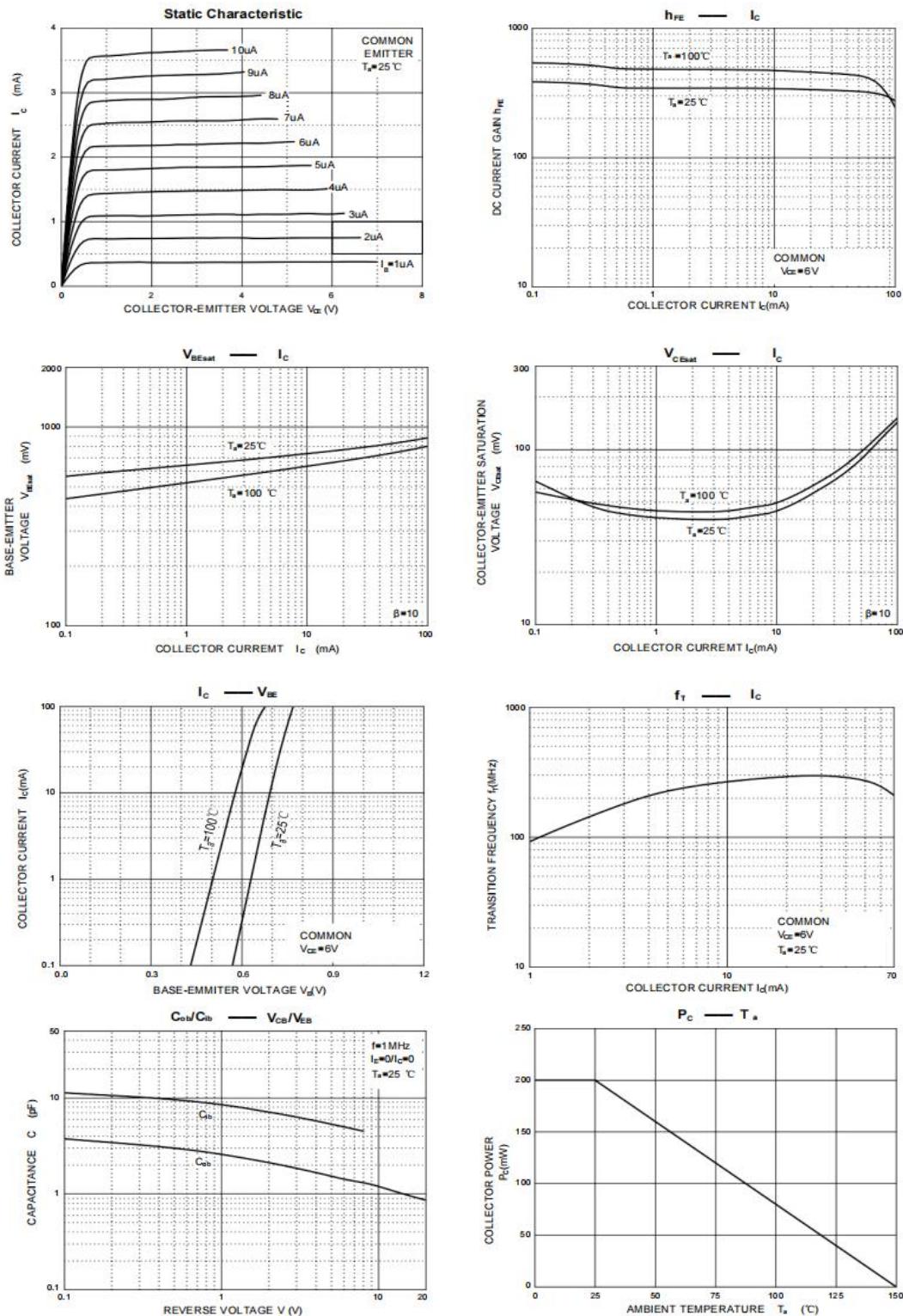
H <sub>FE</sub>		110-220(A)	200-450(B)	420-800(C)
Mark	BC846	1A	1B	1C
	BC847	1E	1F	1G
	BC848	1J	1K	1L

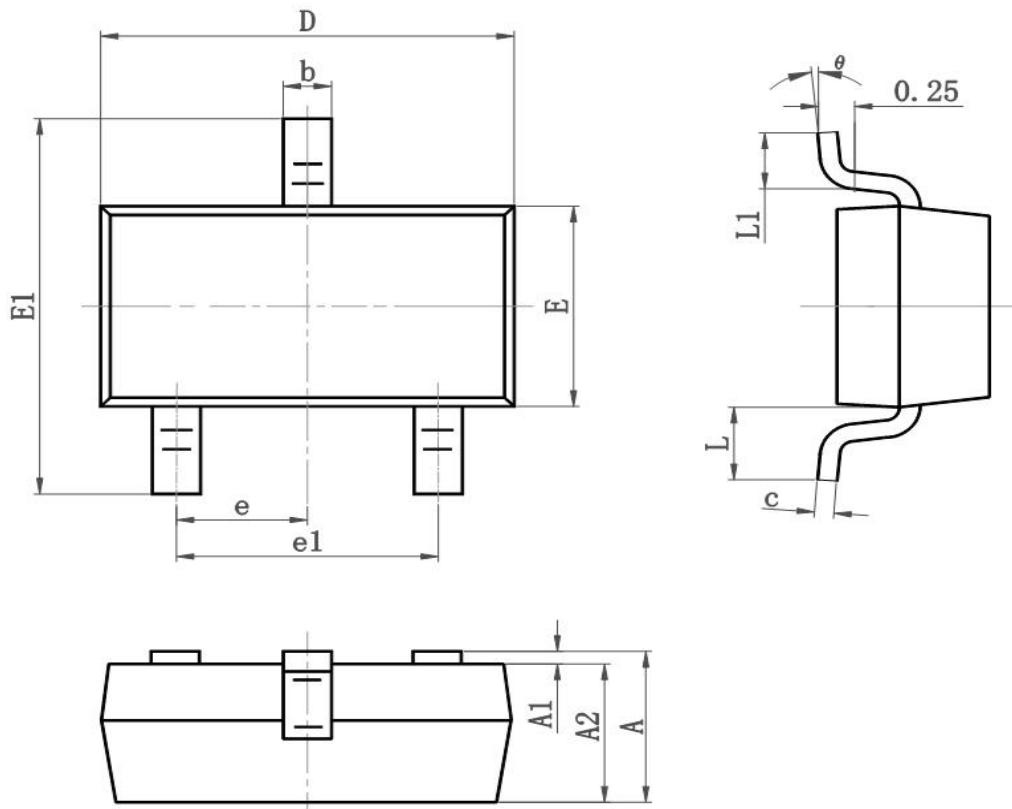
**■ Electrical Characteristics 电特性**

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位	
Collector-Base Breakdown Voltage 集电极基极击穿电压 (IC=10uA, IE=0)	BV <sub>CBO</sub>	80	—	—	V	
		50				
		30				
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压 (IC=10mA, IB=0)	BV <sub>CEO</sub>	65	—	—	V	
		45				
		30				
Emitter-Base Breakdown Voltage 发射极基极击穿电压 (IE=10uA, IC=0)		BV <sub>EBO</sub>	5	—	V	
Collector-Base Leakage Current 集电极基极漏电流	IC <sub>BO</sub>	—	—	100	nA	
BC846A/B/C(V <sub>CB</sub> =70V, IE=0)						
BC847A/B/C(V <sub>CB</sub> =50V, IE=0)						
BC848A/B/C(V <sub>CB</sub> =30V, IE=0)						
Emitter-Base Leakage Current 发射极基极漏电流 (VEB=5V, IC=0)		I <sub>EBO</sub>	—	100	nA	
DC Current Gain 直流电流增益 (V <sub>CE</sub> =5V, IC=2mA)	H <sub>FE</sub>	110	180	220		
BC846B/BC847B/BC848B		200	290	450		
BC846C/BC847C/BC848C		420	520	800		
Collector-Emitter Saturation Voltage 集电极发射极饱和压降 (IC=100mA, IB=5mA)		V <sub>CE(sat)</sub>	—	0.5	V	
Base-Emitter Saturation Voltage 基极发射极饱和压降 (IC=100mA, IB=5mA)		V <sub>BE(sat)</sub>	—	1.1	V	
Transition Frequency 特征频率 (V <sub>CE</sub> =5V, IC=10mA)		f <sub>T</sub>	100	—	MHz	
Output Capacitance 输出电容 (V <sub>CB</sub> =10V, IE=0, f=1MHz)		C <sub>ob</sub>	—	4.5	pF	

■Typical Characteristic Curve 典型特性曲线



**■Dimension 外形封装尺寸**

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.050	0.055
E1	2.250	2.550	0.089	0.100
e	0.900	1.00	0.035	0.039
e1	1.800	2.000	0.071	0.079
L	0.500	0.600	0.020	0.024
L1	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°